

描述 / Descriptions

PDFN5×6 封装 P 沟道场效应管。

P-Channel MOSFET in a PDFN5×6 Plastic Package.

特征 / Features

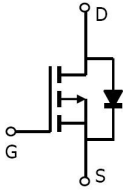
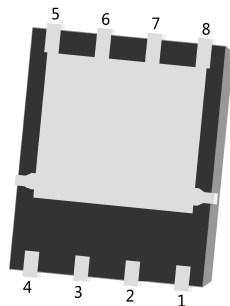
低电阻可最大地降低导电损耗；低栅极电荷，可实现快速切换；低热阻；无卤产品。

Low $R_{DS(ON)}$ to minimize conductive loss; low Gate Charge for fast switching; Low Thermal resistance; HF Product.

用途 / Applications

笔记本电脑交流输入负载开关，电池保护充电/放电。

Notebook AC-in load switch, Battery Protection Charge/Discharge.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1、2、3: S

PIN4: G

PIN5、6、7、8: D

Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

印章代码 / Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings($T_a=25^{\circ}\text{C}$)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V _{DS}	-40	V
Drain Current - Continuous		I _D (T _c =25℃)	-45	A
Drain Current – Pulsed		I _{DM}	-120	A
Gate-Source Voltage		V _{GS}	±20	V
Power Dissipation		P _D (T _c =25℃)	40	W
Single Pulse Avalanche Energy(L=0.5mH)		E _{AS}	317.5	mJ
Avalanche Current(L=0.5mH)		I _{AS}	-31.5	A
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	℃
Thermal resistance, junction - ambient	t ≤ 10s	R _{θJA}	23.6	℃/ W
	Steady-State		55	
Thermal resistance, junction - case	Steady-State	R _{θJC}	3.1	

电性能参数 / Electrical Characteristics($T_a=25^{\circ}\text{C}$)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu\text{A}$ $V_{GS}=0\text{V}$	-40	-48		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40\text{V}$ $V_{GS}=0\text{V}$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu\text{A}$	-1	-1.7	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10\text{V}$, $I_D=-20\text{A}$		11.4	13	m Ω
		$V_{GS}=-4.5\text{V}$, $I_D=-10\text{A}$		15	25	
Diode Forward Voltage	V_{SD}	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$			-1.2	V
Input Capacitance	C_{iss}	$V_{DS}=-25\text{V}$ $V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		4760		pF
Output Capacitance	C_{oss}			2800		
Reverse Transfer Capacitance	C_{rss}			1960		
Gate resistance	R_g	$V_{GS}=0\text{V}$ $V_{DS}=0\text{V}$ $f=1\text{MHz}$		17.5		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10\text{V}$, $V_{DS}=-20\text{V}$, $I_D=-20\text{A}$		34		nC
Total Gate Charge	$Q_{g(4.5V)}$			17.5		
Gate Source Charge	Q_{gs}			5.8		
Gate Drain Charge	Q_{gd}			9		

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DS}=-20V$ $R_L=0.75\ \Omega$ $R_{GEN}=3\ \Omega$		11		ns
Turn-On Rise Time	t_r			7.8		
Turn-Off Delay Time	$t_{d(off)}$			44		
Turn-Off Fall Time	t_f			18		

电参数曲线图 / Electrical Characteristic Curve

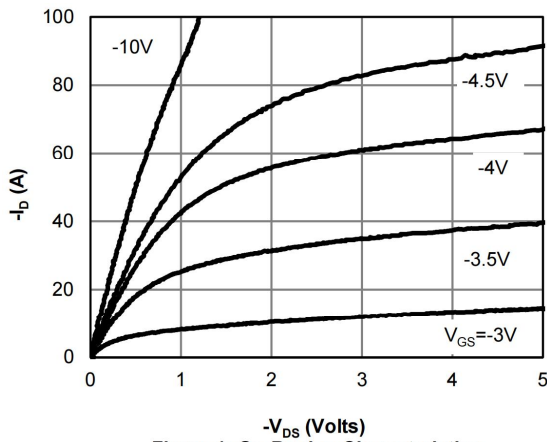


Figure 1: On-Region Characteristics

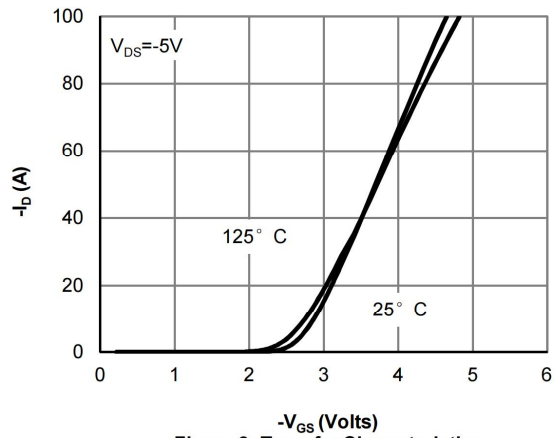


Figure 2: Transfer Characteristics

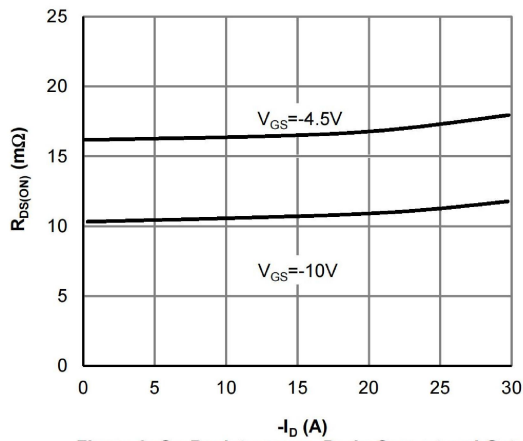


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

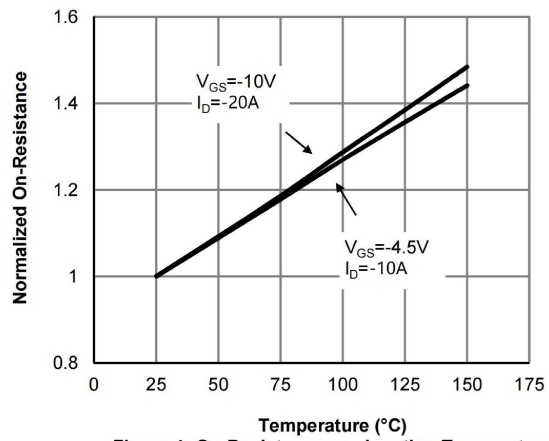


Figure 4: On-Resistance vs. Junction Temperature

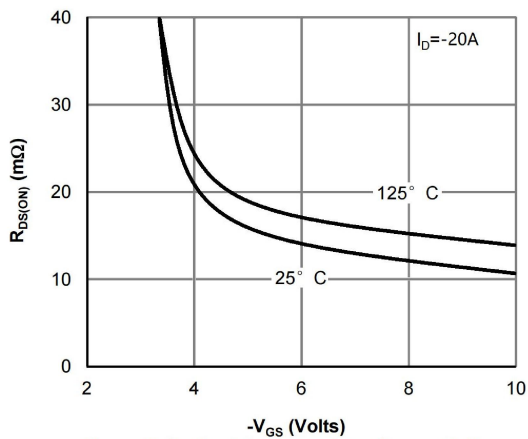


Figure 5: On-Resistance vs. Gate-Source Voltage

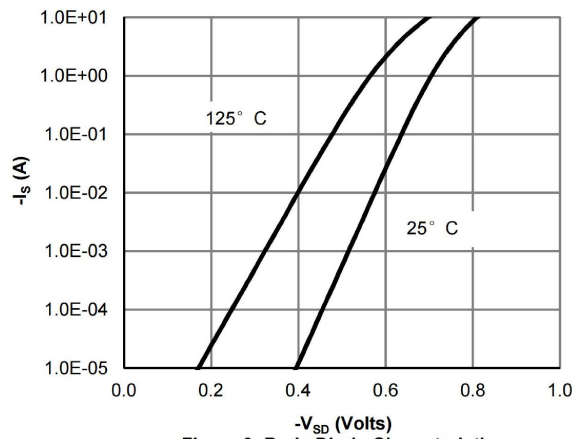


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

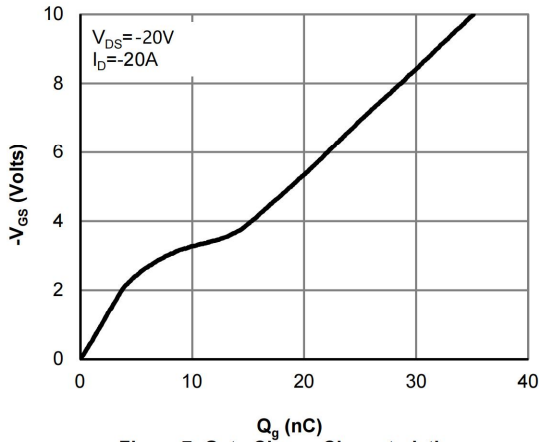


Figure 7: Gate-Charge Characteristics

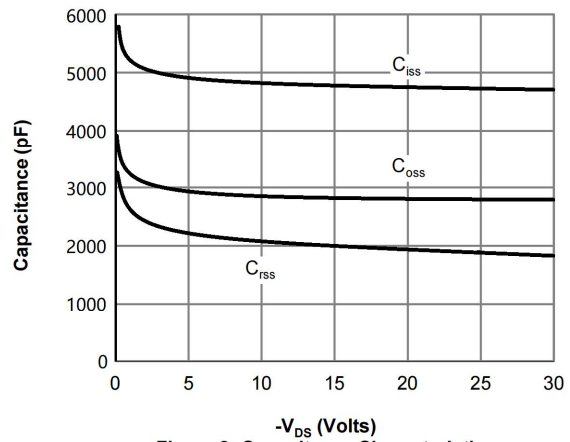


Figure 8: Capacitance Characteristics

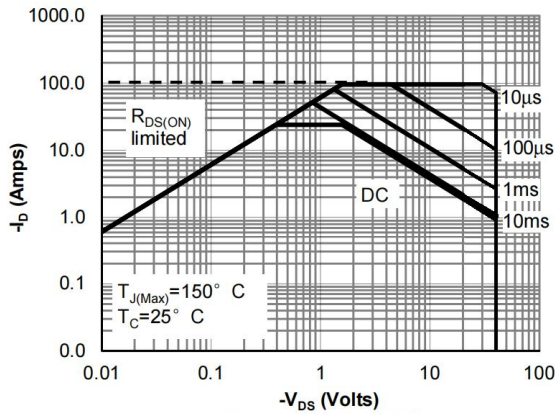


Figure 9: Maximum Forward Biased Safe Operating Area

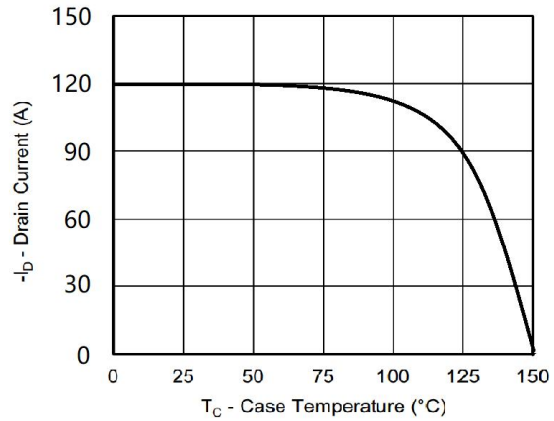


Figure 10: Maximum Continuous Drain Current vs Case Temperature

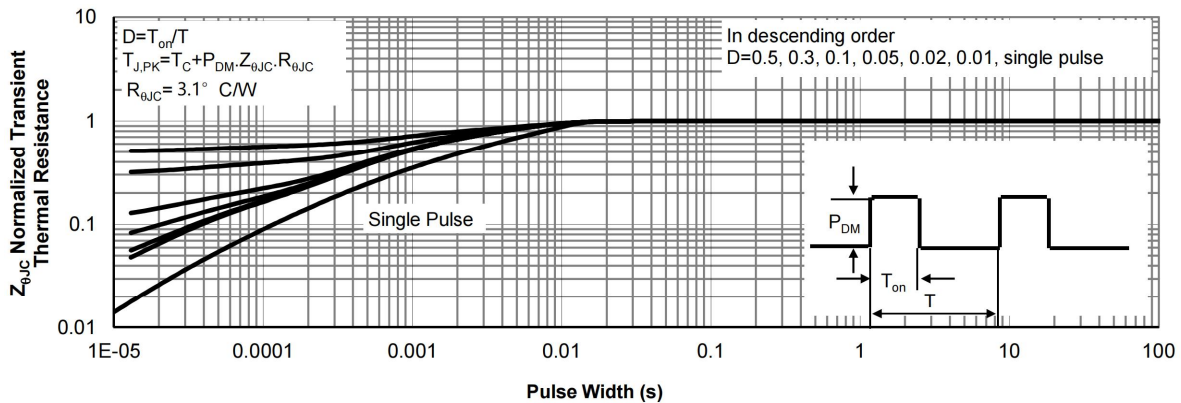
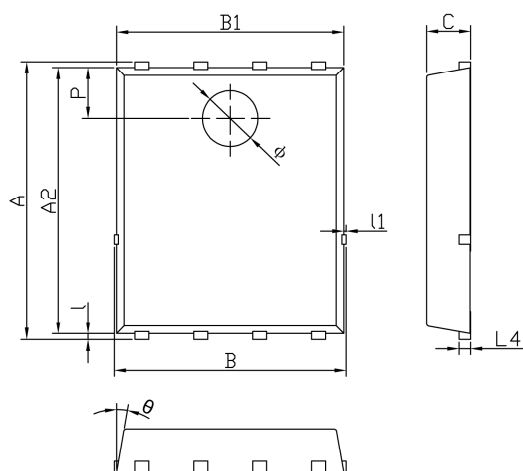


Figure 11: Normalized Maximum Transient Thermal Impedance

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PDFN5 X6

Unit:mm

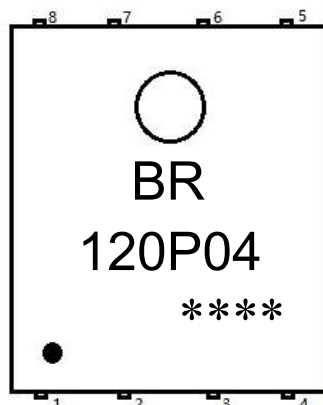


Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	5.90	6.00	6.10
a	3.91	4.01	4.11
A2	5.70	5.75	5.80
B	4.90	5.00	5.10
b	3.37	3.47	3.57
B1	4.80	4.90	5.00
C	0.90	0.95	1.00
L	0.35	0.40	0.45
l	0.06	0.13	0.20
L1	1.10	–	–
l1	–	–	0.10
L2	1.17	1.27	1.37
L4	0.21	0.26	0.34
L6	0.51	0.61	0.71
L7	0.51	0.61	0.71
P	1.00	1.10	1.20
θ	8°	10°	12°
φ	1.10	1.20	1.30

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印章说明 / Marking Instructions



说明：

BR： 为公司代码

120P04： 为产品型号

****： 为生产批号代码，随生产批号变化

Note：

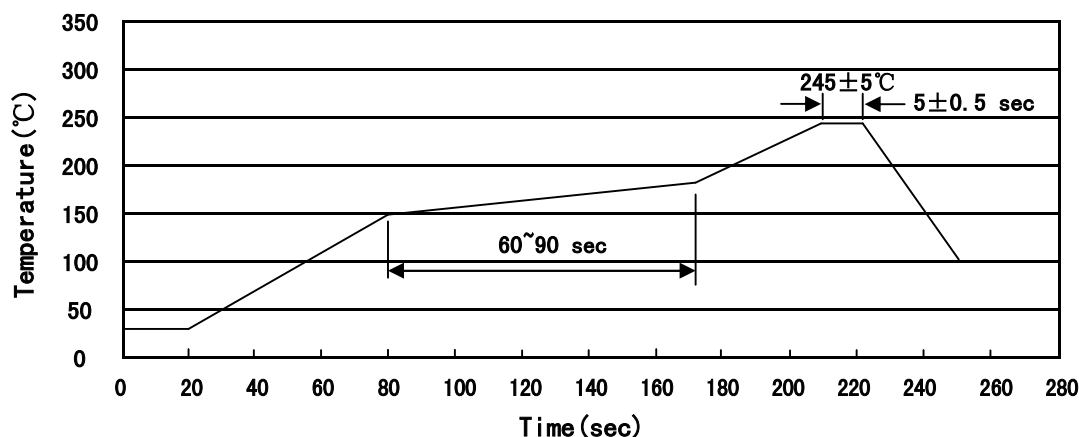
BR： Company Code

120P04： Product Type

****： Lot No. Code, code change with Lot No



回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
PDFN5 × 6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366

使用说明 / Notices